



IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s): Xia Sheng et al

Confirmation No.: 3212

Application No.: 09/845845

Examiner: Santiago, M

Filing Date: Apr 30, 2001

Group Art Unit: 2879

Title: Silicon Emitter With Low Porosity Heavily Doped Contact Layer

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

- ☐ under 37 CFR 1.97(b), or
(Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last)
- ☒ under 37 CFR 1.97 (c) together with either a:
 - ☐ Statement under 37 CFR 1.97(e), or
 - ☒ a \$180.00 fee under 37 CFR 1.17(p), or
(After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs first)
- ☐ under 37 CFR 1.97 (d) together with a:
 - ☐ Statement under 37 CFR 1.97(e)(1) or (2), and
 - ☐ a \$180.00 fee set forth in 37 CFR 1.17(p).
(Filed after final action, a notice of allowance, on or before payment of the issue fee)

Please charge to Deposit Account 08-2025 the sum of \$180.00. At any time during the pendency of this application, please charge any fees required or credit any overpayment to Deposit Account 08-2025 pursuant to 37 CFR 1.25.

☒ Applicant(s) submit herewith Form PTO 1449 - Information Disclosure Statement together with any required copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.

☐ A concise explanation of the relevance of foreign language patents, foreign language publications and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO 1449 and is enclosed herewith.

It is requested that the information disclosed herein be made of record in this application.

☒ I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313-1450. Date of Deposit: April 15 2004

OR

☐ I hereby certify that this paper is being transmitted to the Patent and Trademark Office facsimile number _____ on _____ Number of pages: _____

Typed Name: Alba P Escobar

Signature: [Signature]

Respectfully submitted,

Xia Sheng et al

By Brian R. Short

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Date: April 15, 2004

Telephone No.: 650 857 3870

**PATENT APPLICATION**

Sheet 1 of 1

FORM PTO-1449

**LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT**

(Use several sheets if necessary)

ATTY. DOCKET NO.

10007799-1

APPLICATION NO.

09/845,845

CONFIRMATION NO.

3212

APPLICANT

Xia Sheng, et al.

FILING DATE

April 11, 2002

GROUP

2879**REFERENCE DESIGNATION****U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A				
	1B				
	1C				
	1D				
	1E				
	1F				
	1G				
	1H				
	1I				
	1J				
	1K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L	EP0874384	10/28/1998	PIONEER ELECTRONIC CO		
	1M	EP0913849	05/06/01999	MATSUSHITA ELECTRIC		
	1N	EP1096532	05/02/2001	PIONEER CORP		
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	KOSHIDA N. ET AL.; COLDEMISSION FROM ELECTROLUMINESCENT POROUS SILICON DIODES JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS. TOKYO, JP, VOL. 34, NR. 6A, PART 2, PAGE 705-707 XPOO2067716 ISSN: 0021-4922
	1R	
	1S	

EXAMINER

DATE CONSIDERED